| L Number | Hits | Search Text | DB | Time stamp |
|---|---|---|---|---|
| 1 | 175 | (((257/173,355-358,360-363) or (361/56,111)).CCLS.) and @pd > "20031119" | USPAT; US-PGPUB | 2004/04/10 13:08 |
| 4 | 1 | (reverse adj breakdown) and (breakdown near3 gate adj (oxide insulator)) and @pd > "20031119" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/04/10 13:09 |
| 5 | 65 | reverse adj breakdown and @pd > "20031119" | USPAT; US-PGPUB | 2004/04/10 13:09 |
| 6 | 310 | protection with diode and @pd > "20031119" | USPAT; US-PGPUB | 2004/04/10 13:10 |
| 7 | 67 | breakdown near3 gate adj (oxide insulator) and @pd > "20031119" | USPAT; US-PGPUB | 2004/04/10 13:10 |
| 8 | 67 | breakdown near3 gate adj (oxide insulator) and @pd > "20031119" | USPAT; US-PGPUB | 2004/04/10 13:10 |
| 9 | 2 | core adj region and I/O adj region and @pd > "20031119" | USPAT; US-PGPUB | 2004/04/10 13:10 |
| 10 | 178 | input adj pad and @pd > "20031119" | USPAT; US-PGPUB | 2004/04/10 13:11 |
| 11 | 13 | ((reverse adj breakdown) and input) and (protection with diode) and @pd > "20031119" | USPAT; US-PGPUB | 2004/04/10 13:11 |
| 12 | 0 | (protection with diode and cmos) and core adj region and @pd > "20031119" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/04/10 13:11 |
| 13 | 98 | (257/173,355-358,360-363 or 361/56,111).CCLS. and (esd electrostatic adj discharge) and @pd > "20031119" | USPAT; US-PGPUB | 2004/04/10 13:13 |
| 3 | 98 | (((((257/173,355-358,360-363) or (361/56,111)).CCLS.) and @pd > "20030619") and (esd electrostatic adj discharge) and @pd > "20031119" | USPAT; US-PGPUB | 2004/04/10 13:14 |
| 14 | 601 | (((((257/173,355-358,360-363) or (361/56,111)).CCLS.) and @pd > "20031119") (((((257/360|257/361|257/362|257/363 | 257/355|257/356|257/357|257/358 | 257/173) or (361/111 | 361/56)).CCLS.) and @pd > "20030619") and (esd electrostatic adj discharge) and @pd > "20031119") (((((257/173,355-358,360-363) or (361/56,111)).CCLS.) and @pd > "20030619") and (esd electrostatic adj discharge) and @pd > "20031119") ((reverse adj breakdown) and (breakdown near3 gate adj (oxide insulator)) and @pd > "20031119") (reverse adj breakdown and @pd > "20031119") (protection with diode and @pd > "20031119") (breakdown near3 gate adj (oxide insulator) and @pd > "20031119") (breakdown near3 gate adj (oxide insulator) and @pd > "20031119") (core adj region and I/O adj region and @pd > "20031119") (input adj pad and @pd > "20031119") (((reverse adj breakdown) and input) and (protection with diode) and @pd > "20031119") ((protection with diode and cmos) and core adj region and @pd > "20031119") ((257/173,355-358,360-363 or 361/56,111).CCLS. and (esd electrostatic adj discharge) and @pd > "20031119")) and (voltage volt) | USPAT; US-PGPUB | 2004/04/10 13:15 |
| 15 | 242 | (((((257/173,355-358,360-363) or (361/56,111)).CCLS.) and @pd > "20031119") (((((257/360|257/361|257/362|257/363 | 257/355|257/356|257/357|257/358 | 257/173) or (361/111 | 361/56)).CCLS.) and @pd > "20030619") and (esd electrostatic adj discharge) and @pd > "20031119") (((((257/173,355-358,360-363) or (361/56,111)).CCLS.) and @pd > "20030619") and (esd electrostatic adj discharge) and @pd > "20031119") ((reverse adj breakdown) and (breakdown near3 gate adj (oxide insulator)) and @pd > "20031119") (reverse adj breakdown and @pd > "20031119") (protection with diode and @pd > "20031119") (breakdown near3 gate adj (oxide insulator) and @pd > "20031119") (breakdown near3 gate adj (oxide insulator) and @pd > "20031119") (core adj region and I/O adj region and @pd > "20031119") (input adj pad and @pd > "20031119") (((reverse adj breakdown) and input) and (protection with diode) and @pd > "20031119") ((protection with diode and cmos) and core adj region and @pd > "20031119") ((257/173,355-358,360-363 or 361/56,111).CCLS. and (esd electrostatic adj discharge) and @pd > "20031119")) and (volts volt) | USPAT; US-PGPUB | 2004/04/10 13:15 |